

IN THE CLAIMS:

Please cancel claims 12, 13, 24, and 32-34 without prejudice, and amend the claims as follows:

1-7. (Canceled)

8. (Currently Amended) A method for planarizing an organosilicate layer, comprising:

positioning a substrate having an organosilicate layer thereon in a polishing system;

providing a slurry including silica as an abrasive material selected from the group consisting of silica (SiO₂), aluminum oxide (Al₂O₃), zirconium oxide (ZrO₂), titanium oxide (TiO₂), and combinations thereof dispersed in a solvent to the polishing system, wherein the slurry has a pH greater than of about 9.0 10 or greater; and

polishing the organosilicate layer using the slurry.

9. (Canceled)

10. (Original) The method of claim 8 wherein the abrasive material has an average particle size greater than about 35 nm (nanometers).

11. (Currently Amended) The method of claim 8 wherein the pH of the slurry is adjusted by adding a source of hydroxyl ions potassium hydroxide (KOH) or ammonium hydroxide (NH₄OH) thereto.

12-13. (Canceled)

14. (Currently Amended) The method of claim 8 wherein the concentration of abrasive material in the slurry is within a range of about 10% 22% by weight to about 60% 30% by weight.

15. (Original) The method of claim 8 wherein the organosilicate layer is polished by placing it in contact with a polishing pad, the polishing pad having the slurry thereon, and wherein the polishing pad is disposed upon a rotatable platen.

16. (Original) The method of claim 15 wherein the polishing pad comprises polyurethane.

17. (Original) The method of claim 15 wherein the organosilicate layer contacts the polishing pad with a pressure within range of about 1 psi (pounds/square inch) to about 14 psi.

18. (Original) The method of claim 15 wherein the platen rotates at a speed within the range of about 0.1 m/s (meters/second) to about 2 m/s.

19. (Currently Amended) A method for fabricating a device, comprising:
providing a substrate having conductive features formed thereon with an organosilicate layer deposited between and on top of the conductive features;
positioning the substrate in a polishing system;
providing a slurry including silica as an abrasive material selected from the group consisting of silica (SiO_2), aluminum oxide (Al_2O_3), zirconium oxide (ZrO_2), titanium oxide (TiO_2), and combinations thereof dispersed in a solvent and potassium hydroxide (KOH) to the polishing system, wherein the slurry has a pH greater than of about 9 10 or greater; and
polishing the organosilicate layer using the slurry.

20. (Canceled)

21. (Original) The method of claim 19 wherein the abrasive material has an average particle size greater than about 35 nm (nanometers).

22-24. (Canceled)

25. (Currently Amended) The method of claim 19 wherein the concentration of abrasive material in the slurry is within a range of about 10% 22% by weight to about 60% 30% by weight.

26. (Original) The method of claim 19 wherein the organosilicate layer is polished by placing it in contact with a polishing pad having the slurry thereon, and wherein the polishing pad is disposed upon a rotatable platen.

27. (Original) The method of claim 26 wherein the polishing pad comprises polyurethane.

28. (Original) The method of claim 26 wherein the organosilicate layer contacts the polishing pad with a pressure within a range of about 1 psi (pounds/square inch) to about 4 psi.

29. (Original) The method of claim 26 wherein the platen rotates at a speed within a range of about 0.1 m/s (meters/second) to about 2.0 m/s.

30. (Currently Amended) A method for planarizing an organosilicate layer, comprising:

positioning a substrate having an organosilicate layer thereon in a polishing system;

providing a slurry including silica as an abrasive material selected from the group consisting of silica (SiO₂), aluminum oxide (Al₂O₃), zirconium oxide (ZrO₂), titanium oxide (TiO₂), and combinations thereof having an average particle size greater than about 35 nm and dispersed in a solvent and potassium hydroxide (KOH) or ammonium

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hydroxide (NH₄OH) to the polishing system, wherein the slurry has a pH greater than or about 9.0 10 or greater and the concentration of the abrasive material in the slurry is within a range of about 10% 22% by weight to about 60% 30% by weight; and polishing the organosilicate layer using the slurry.

31-34. (Canceled)

35. (Previously Presented) The method of claim 30, wherein the organosilicate layer is polished by placing it in contact with a polishing pad, the polishing pad having the slurry thereon, and wherein the polishing pad is disposed upon a rotatable platen.

36. (Previously Presented) The method of claim 35, wherein the organosilicate layer contacts the polishing pad with a pressure within range of about 1 psi (pounds/square inch) to about 14 psi.